



Form 1449 (Modified) Information Disclosure Statement By Applicant (Use Several Sheets if Necessary)	Atty Docket No.	Application No.:
	UNTYP027	10/665,882
	Applicant:	
	RINERSON et al.	
Filing Date	Group	
September 19, 2003	2811	

U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
JH	A1	6,204,139	3/2001	Liu et al.	438	305	

Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation	
							Yes	No
	B1							

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
JH	C1	Baikalov et al., "Field-Driven Hysteric and Reversible Resistive Switch at the Ag Pro _{0.7} Ca _{0.3} MnO ₃ Interface", May 2003, Department of Physics and Texas Center for Superconductivity, University of Houston, pp. 1-8.
JH	C2	Beck et al., "Reproducible switching effect in thin oxide films for memory applications", July 2000, Applied Physics Letters, Vol. 77, No. 1, pp. 139-141.
JH	C3	Gerstner et al., "Nonvolatile memory effects in nitrogen doped tetrahedral amorphous carbon thin films," November 1998, Journal of Applied Physics, Vol. 84, No. 10, pp. 5647-5651.
JH	C4	Mieville et al., "Transport across conducting ferromagnetic oxide/metal interfaces", September 1998, Applied Physics Letters, Vol. 73, No. 12, pp. 1736-1738.
JH	C5	Liu et al., "A New Concept for Non-Volatile Memory: The Electric-Pulse Induced Resistive Change Effect in Colossal Magnetoresistive Thin Films", University of Houston, pp. 1-7.
JH	C6	Liu et al., "Electric-pulse-induced reversible resistance change effect in magnetoresistive films", May 2000, Applied Physics Letters, Vol. 76, No. 19, pp. 2749-2751.
JH	C7	Plecken et al., "Degradation of LaMnO _{3-y} surface layer in LaMnO _{3-y} /metal interface", July 2002, Applied Physics Letters, Vol. 81, No. 5, pp. 859-861.
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9/24	C12	Watanabe et al., "Current-driver insulator-conductor transition and nonvolatile memory in chromium-doped SrTiO_3 single crystals," June 2001, Applied Physics Letters, Vol. 78, No. 23, pp. 3738-3740.
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Examiner		Date Considered
JSC E. Hunt		9/29/04

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.